

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L20	3	((first or second) adj gate adj electrode) near5 between near5 (first adj gate adj (insulating or dielectric)) near5 (second adj gate adj (insulating or dielectric)) and (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:44
L21	95	(gate adj electrode) near between near (gate adj (insulating or dielectric) adj film) and (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:44
L22	33	(gate adj electrode) near between near (gate adj (insulating or dielectric) adj film) same (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:44
L23	13	((gate adj electrode) near between near (gate adj (insulating or dielectric) adj film) same (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:45
L24	0	((gate adj electrode) near between near ((first or second) adj gate adj (insulating or dielectric) adj film) same (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:45
L25	0	((gate adj electrode) near between near ((first or second) adj gate adj (insulating or dielectric) adj film) same (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:45
L26	3	((gate adj electrode) near2 between near2 ((first or second) adj gate adj (insulating or dielectric) adj film) same (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 18:45